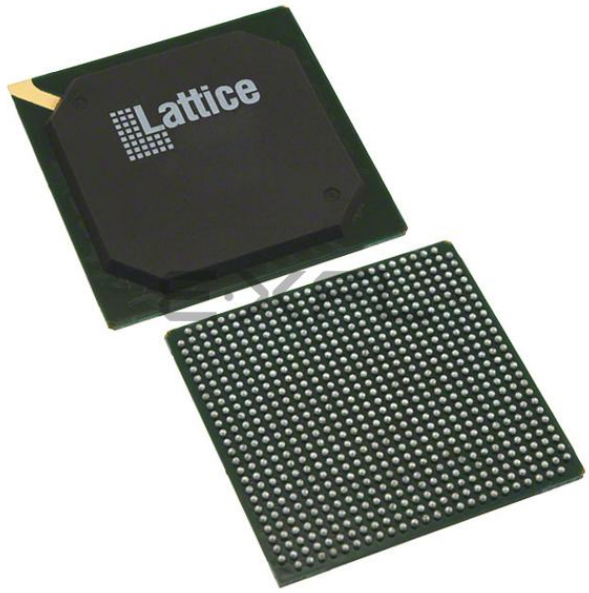
Lattice Semiconductor Corporation - LFE3-150EA-8FN672C Datasheet



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Understanding Embedded - FPGAs (Field Programmable Gate Array)

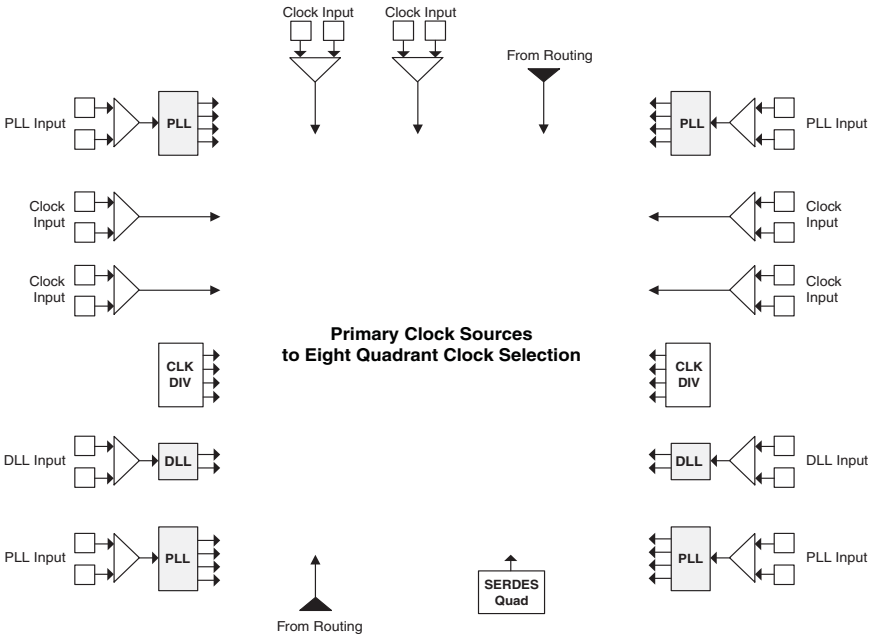
Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

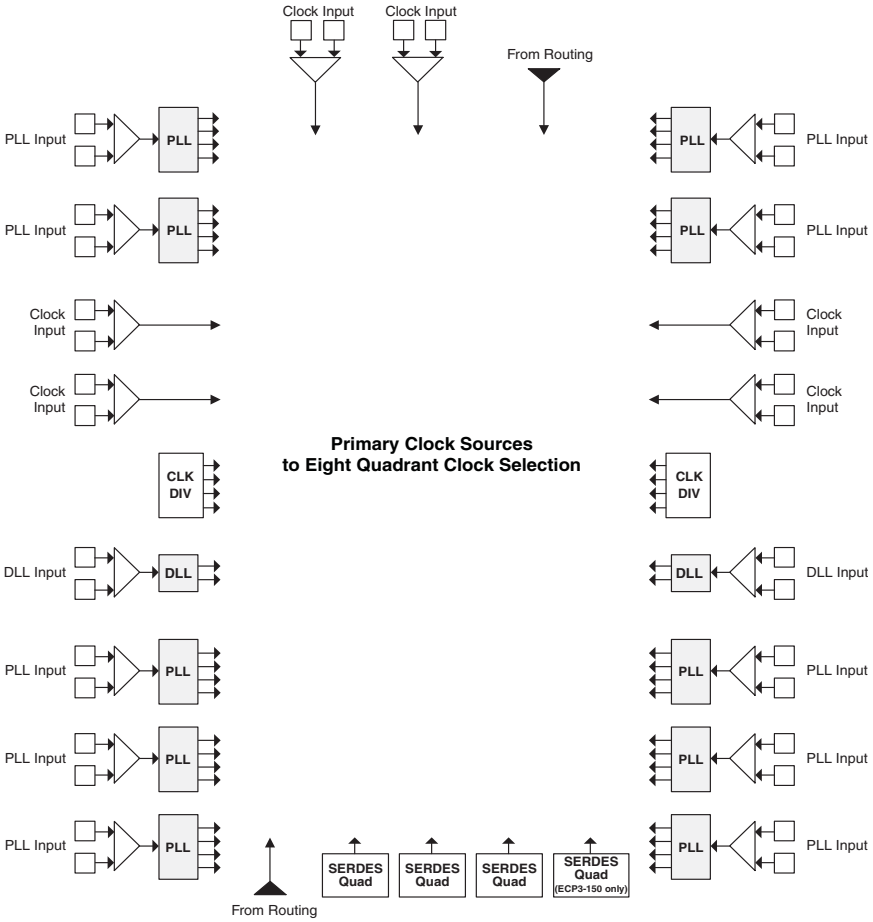
Details	
Product Status	Active
Number of LABs/CLBs	18625
Number of Logic Elements/Cells	149000
Total RAM Bits	7014400
Number of I/O	380
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	672-BBGA
Supplier Device Package	672-FPBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe3-150ea-8fn672c

Figure 2-10. Primary Clock Sources for LatticeECP3-35



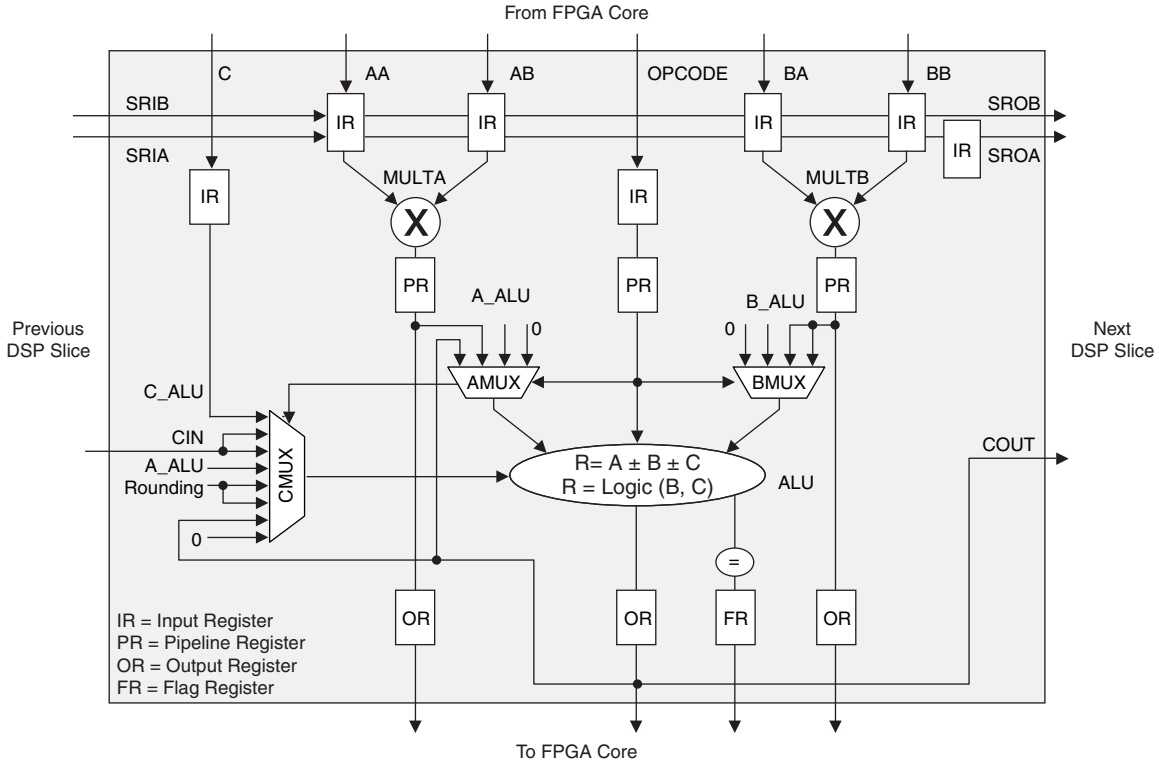
Note: Clock inputs can be configured in differential or single-ended mode.

Figure 2-11. Primary Clock Sources for LatticeECP3-70, -95, -150



Note: Clock inputs can be configured in differential or single-ended mode.

Figure 2-25. Detailed sysDSP Slice Diagram



Note: A_ALU, B_ALU and C_ALU are internal signals generated by combining bits from AA, AB, BA BB and C inputs. See TN1182, LatticeECP3 sysDSP Usage Guide, for further information.

The LatticeECP2 sysDSP block supports the following basic elements.

- MULT (Multiply)
- MAC (Multiply, Accumulate)
- MULTADDSUB (Multiply, Addition/Subtraction)
- MULTADDSUBSUM (Multiply, Addition/Subtraction, Summation)

Table 2-8 shows the capabilities of each of the LatticeECP3 slices versus the above functions.

Table 2-8. Maximum Number of Elements in a Slice

Width of Multiply	x9	x18	x36
MULT	4	2	1/2
MAC	1	1	—
MULTADDSUB	2	1	—
MULTADDSUBSUM	1[1]	1/2	—

1. One slice can implement 1/2 9x9 m9x9addsubsum and two m9x9addsubsum with two slices.

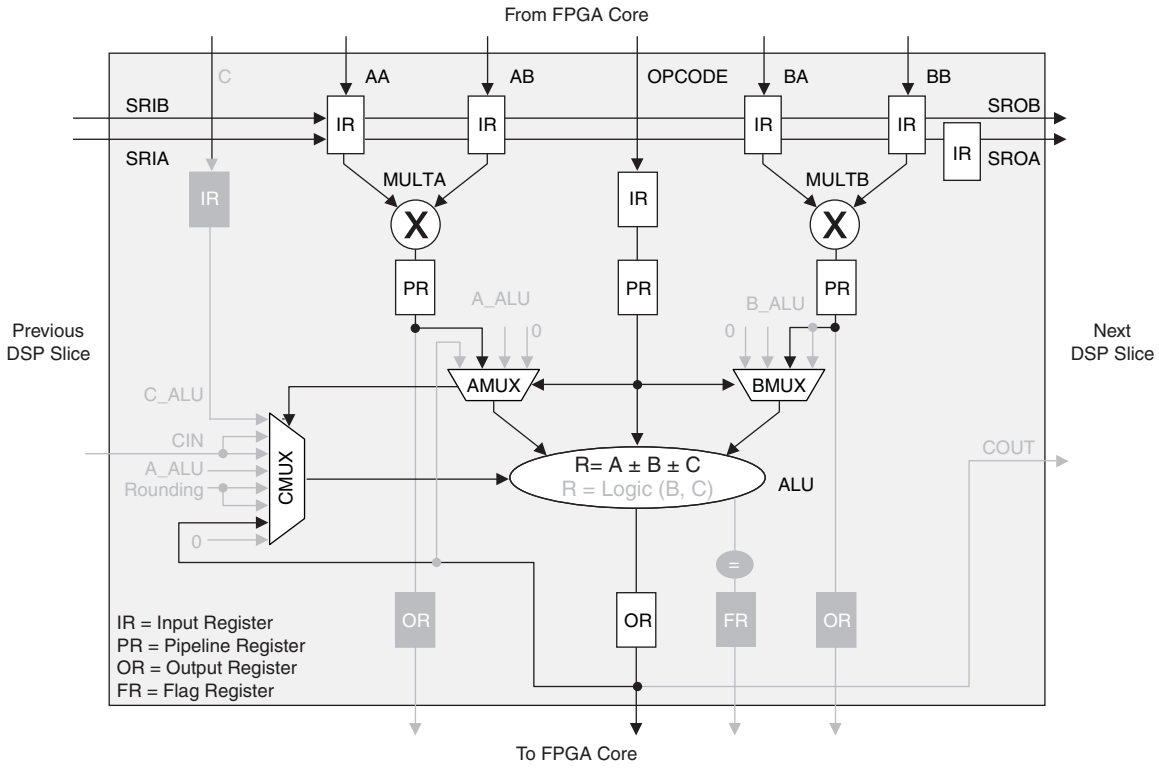
Some options are available in the four elements. The input register in all the elements can be directly loaded or can be loaded as a shift register from previous operand registers. By selecting “dynamic operation” the following operations are possible:

- In the Add/Sub option the Accumulator can be switched between addition and subtraction on every cycle.
- The loading of operands can switch between parallel and serial operations.

MMAC DSP Element

The LatticeECP3 supports a MAC with two multipliers. This is called Multiply Multiply Accumulate or MMAC. In this case, the two operands, AA and AB, are multiplied and the result is added with the previous accumulated value and with the result of the multiplier operation of operands BA and BB. This accumulated value is available at the output. The user can enable the input and pipeline registers, but the output register is always enabled. The output register is used to store the accumulated value. The ALU is configured as the accumulator in the sysDSP slice. A registered overflow signal is also available. The overflow conditions are provided later in this document. Figure 2-28 shows the MMAC sysDSP element.

Figure 2-28. MMAC sysDSP Element



To accomplish write leveling in DDR3, each DQS group has a slightly different delay that is set by DYN DELAY[7:0] in the DQS Write Control logic block. The DYN DELAY can set 128 possible delay step settings. In addition, the most significant bit will invert the clock for a 180-degree shift of the incoming clock.

LatticeECP3 input and output registers can also support DDR gearing that is used to receive and transmit the high speed DDR data from and to the DDR3 Memory.

LatticeECP3 supports the 1.5V SSTL I/O standard required for the DDR3 memory interface. For more information, refer to the sysIO section of this data sheet.

Please see TN1180, LatticeECP3 High-Speed I/O Interface for more information on DDR Memory interface implementation in LatticeECP3.

sysI/O Buffer

Each I/O is associated with a flexible buffer referred to as a sysI/O buffer. These buffers are arranged around the periphery of the device in groups referred to as banks. The sysI/O buffers allow users to implement the wide variety of standards that are found in today's systems including LVDS, BLVDS, HSTL, SSTL Class I & II, LVCMOS, LVTTL, LVPECL, PCI.

sysI/O Buffer Banks

LatticeECP3 devices have six sysI/O buffer banks: six banks for user I/Os arranged two per side. The banks on the bottom side are wraparounds of the banks on the lower right and left sides. The seventh sysI/O buffer bank (Configuration Bank) is located adjacent to Bank 2 and has dedicated/shared I/Os for configuration. When a shared pin is not used for configuration it is available as a user I/O. Each bank is capable of supporting multiple I/O standards. Each sysI/O bank has its own I/O supply voltage (V_{CCIO}). In addition, each bank, except the Configuration Bank, has voltage references, V_{REF1} and V_{REF2}, which allow it to be completely independent from the others. Figure 2-38 shows the seven banks and their associated supplies.

In LatticeECP3 devices, single-ended output buffers and ratioed input buffers (LVTTL, LVCMOS and PCI) are powered using V_{CCIO}. LVTTL, LVCMOS33, LVCMOS25 and LVCMOS12 can also be set as fixed threshold inputs independent of V_{CCIO}.

Each bank can support up to two separate V_{REF} voltages, V_{REF1} and V_{REF2}, that set the threshold for the referenced input buffers. Some dedicated I/O pins in a bank can be configured to be a reference voltage supply pin. Each I/O is individually configurable based on the bank's supply and reference voltages.

Figure 2-40. SERDES/PCS Quads (LatticeECP3-150)

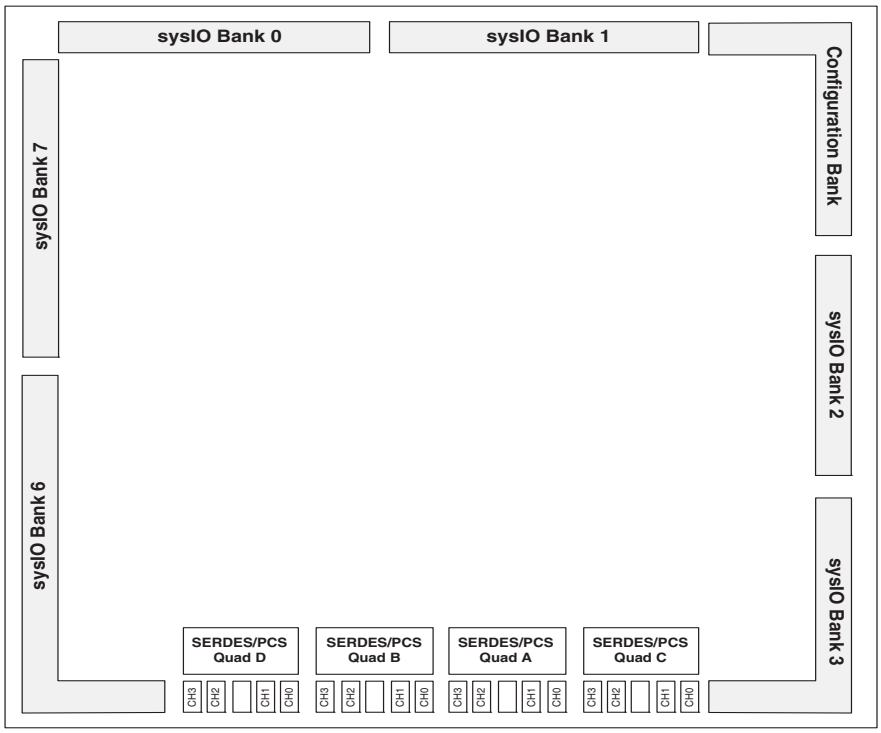


Table 2-13. LatticeECP3 SERDES Standard Support

Standard	Data Rate (Mbps)	Number of General/Link Width	Encoding Style
PCI Express 1.1	2500	x1, x2, x4	8b10b
Gigabit Ethernet	1250, 2500	x1	8b10b
SGMII	1250	x1	8b10b
XAUI	3125	x4	8b10b
Serial RapidIO Type I, Serial RapidIO Type II, Serial RapidIO Type III	1250, 2500, 3125	x1, x4	8b10b
CPRI-1, CPRI-2, CPRI-3, CPRI-4	614.4, 1228.8, 2457.6, 3072.0	x1	8b10b
SD-SDI (259M, 344M)	143[1], 177[1], 270, 360, 540	x1	NRZI/Scrambled
HD-SDI (292M)	1483.5, 1485	x1	NRZI/Scrambled
3G-SDI (424M)	2967, 2970	x1	NRZI/Scrambled
SONET-STS-3[2]	155.52	x1	N/A
SONET-STS-12[2]	622.08	x1	N/A
SONET-STS-48[2]	2488	x1	N/A

1. For slower rates, the SERDES are bypassed and CML signals are directly connected to the FPGA routing.
2. The SONET protocol is supported in 8-bit SERDES mode. See TN1176 Lattice ECP3 SERDES/PCS Usage Guide for more information.

LatticeECP3 Family Data Sheet DC and Switching Characteristics

April 2014 Data Sheet DS1021

Absolute Maximum Ratings[1, 2, 3]

Supply Voltage V_{CC} . . . . . –0.5 V to 1.32 V

Supply Voltage V_{CCAUX} . . . . . –0.5 V to 3.75 V

Supply Voltage V_{CCJ} . . . . . –0.5 V to 3.75 V

Output Supply Voltage V_{CCIO} . . . . . –0.5 V to 3.75 V

Input or I/O Tristate Voltage Applied[4]. . . –0.5 V to 3.75 V

Storage Temperature (Ambient) . . . . . .–65 V to 150 °C

Junction Temperature (T_J) . . . . . .+125 °C

1. Stress above those listed under the "Absolute Maximum Ratings" may cause permanent damage to the device. Functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.
2. Compliance with the Lattice Thermal Management document is required.
3. All voltages referenced to GND.
4. Overshoot and undershoot of –2 V to (V_{IHMAX} + 2) volts is permitted for a duration of <20 ns.

Recommended Operating Conditions[1]

Symbol	Parameter	Min.	Max.	Units
V_{CC}[2]	Core Supply Voltage	1.14	1.26	V
V_{CCAUX}[2, 4]	Auxiliary Supply Voltage, Terminating Resistor Switching Power Supply (SERDES)	3.135	3.465	V
V_{CCPLL}	PLL Supply Voltage	3.135	3.465	V
V_{CCIO}[2, 3]	I/O Driver Supply Voltage	1.14	3.465	V
V_{CCJ}[2]	Supply Voltage for IEEE 1149.1 Test Access Port	1.14	3.465	V
V_{REF1} and V_{REF2}	Input Reference Voltage	0.5	1.7	V
V_{TT}[5]	Termination Voltage	0.5	1.3125	V
t_{JCOM}	Junction Temperature, Commercial Operation	0	85	°C
t_{JIND}	Junction Temperature, Industrial Operation	-40	100	°C
SERDES External Power Supply[6]				
V_{CCIB}	Input Buffer Power Supply (1.2 V)	1.14	1.26	V
	Input Buffer Power Supply (1.5 V)	1.425	1.575	V
V_{CCOB}	Output Buffer Power Supply (1.2 V)	1.14	1.26	V
	Output Buffer Power Supply (1.5 V)	1.425	1.575	V
V_{CCA}	Transmit, Receive, PLL and Reference Clock Buffer Power Supply	1.14	1.26	V

1. For correct operation, all supplies except V_{REF} and V_{TT} must be held in their valid operation range. This is true independent of feature usage.
2. If V_{CCIO} or V_{CCJ} is set to 1.2 V, they must be connected to the same power supply as V_{CC}. If V_{CCIO} or V_{CCJ} is set to 3.3 V, they must be connected to the same power supply as V_{CCAUX}.
3. See recommended voltages by I/O standard in subsequent table.
4. V_{CCAUX} ramp rate must not exceed 30 mV/µs during power-up when transitioning between 0 V and 3.3 V.
5. If not used, V_{TT} should be left floating.
6. See TN1176, LatticeECP3 SERDES/PCS Usage Guide for information on board considerations for SERDES power supplies.

Hot Socketing Specifications[1, 2, 3]

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
IDK_HS[4]	Input or I/O Leakage Current	$0 \le V_{IN} \le V_{IH}$ (Max.)	—	—	+/–1	mA
IDK[5]	Input or I/O Leakage Current	$0 \le V_{IN} < V_{CCIO}$	—	—	+/–1	mA
		$V_{CCIO} \le V_{IN} \le V_{CCIO}$ + 0.5V	—	18	—	mA

1. V_{CC}, V_{CCAUX} and V_{CCIO} should rise/fall monotonically.
2. I_{DK} is additive to I_{PU}, I_{PD} or I_{BH}.
3. LVCMOS and LVTTL only.
4. Applicable to general purpose I/O pins located on the top and bottom sides of the device.
5. Applicable to general purpose I/O pins located on the left and right sides of the device.

Hot Socketing Requirements[1, 2]

Description	Min.	Typ.	Max.	Units
Input current per SERDES I/O pin when device is powered down and inputs driven.	—	—	8	mA

1. Assumes the device is powered down, all supplies grounded, both P and N inputs driven by CML driver with maximum allowed VCCOB (1.575 V), 8b10b data, internal AC coupling.
2. Each P and N input must have less than the specified maximum input current. For a 16-channel device, the total input current would be 8 mA*16 channels *2 input pins per channel = 256 mA

ESD Performance

Please refer to the LatticeECP3 Product Family Qualification Summary for complete qualification data, including ESD performance.

DC Electrical Characteristics

Over Recommended Operating Conditions

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
I_{IL}, I_{IH}[1, 4]	Input or I/O Low Leakage	$0 \le V_{IN} \le (V_{CCIO} - 0.2\ V)$	—	—	10	µA
I_{IH}[1, 3]	Input or I/O High Leakage	$(V_{CCIO} - 0.2\ V) < V_{IN} \le 3.6\ V$	—	—	150	µA
I_{PU}	I/O Active Pull-up Current	$0 \le V_{IN} \le 0.7\ V_{CCIO}$	–30	—	–210	µA
I_{PD}	I/O Active Pull-down Current	V_{IL} (MAX) $\le V_{IN} \le V_{CCIO}$	30	—	210	µA
I_{BHLS}	Bus Hold Low Sustaining Current	$V_{IN} = V_{IL}$ (MAX)	30	—	—	µA
I_{BHHS}	Bus Hold High Sustaining Current	$V_{IN} = 0.7\ V_{CCIO}$	–30	—	—	µA
I_{BHLO}	Bus Hold Low Overdrive Current	$0 \le V_{IN} \le V_{CCIO}$	—	—	210	µA
I_{BHHO}	Bus Hold High Overdrive Current	$0 \le V_{IN} \le V_{CCIO}$	—	—	–210	µA
V_{BHT}	Bus Hold Trip Points	$0 \le V_{IN} \le V_{IH}$ (MAX)	V_{IL} (MAX)	—	V_{IH} (MIN)	V
C1	I/O Capacitance[2]	V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = 1.2 V, V_{IO} = 0 to V_{IH} (MAX)	—	5	8	pf
C2	Dedicated Input Capacitance[2]	V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = 1.2 V, V_{IO} = 0 to V_{IH} (MAX)	—	5	7	pf

1. Input or I/O leakage current is measured with the pin configured as an input or as an I/O with the output driver tri-stated. It is not measured with the output driver active. Bus maintenance circuits are disabled.
2. T_A 25 °C, f = 1.0 MHz.
3. Applicable to general purpose I/Os in top and bottom banks.
4. When used as V_{REF}, maximum leakage= 25 µA.

BLVDS25

The LatticeECP3 devices support the BLVDS standard. This standard is emulated using complementary LVCMOS outputs in conjunction with a parallel external resistor across the driver outputs. BLVDS is intended for use when multi-drop and bi-directional multi-point differential signaling is required. The scheme shown in Figure 3-2 is one possible solution for bi-directional multi-point differential signals.

Figure 3-2. BLVDS25 Multi-point Output Example

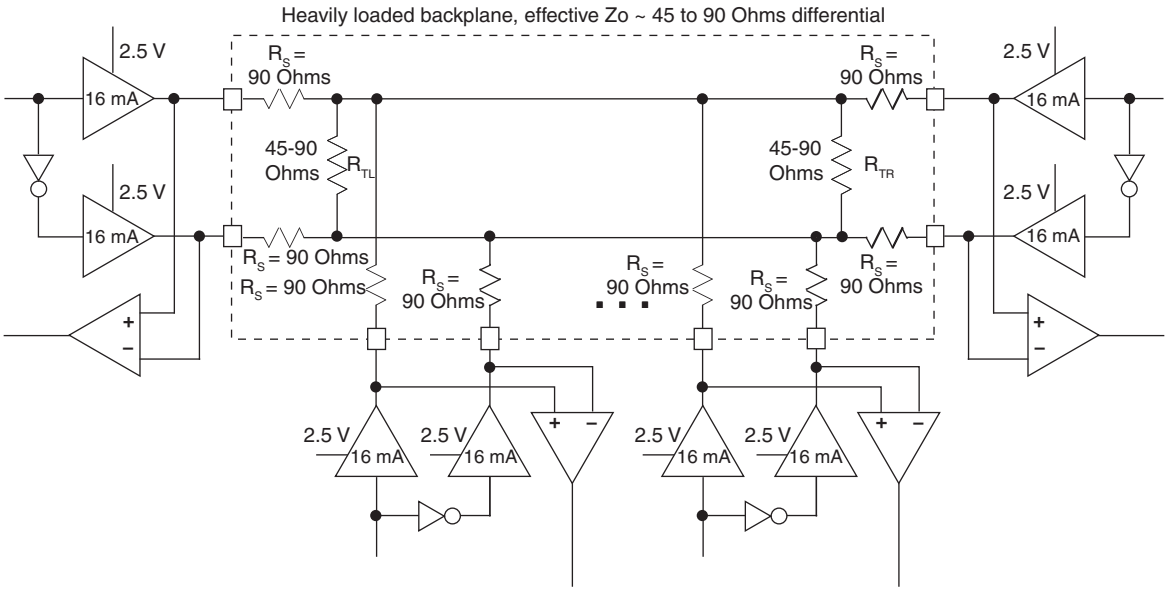


Table 3-2. BLVDS25 DC Conditions[1]

Over Recommended Operating Conditions

Parameter	Description	Typical		Units
		Zo = 45Ω	Zo = 90Ω	
V_{CCIO}	Output Driver Supply (+/– 5%)	2.50	2.50	V
Z_{OUT}	Driver Impedance	10.00	10.00	Ω
R_S	Driver Series Resistor (+/– 1%)	90.00	90.00	Ω
R_{TL}	Driver Parallel Resistor (+/– 1%)	45.00	90.00	Ω
R_{TR}	Receiver Termination (+/– 1%)	45.00	90.00	Ω
V_{OH}	Output High Voltage	1.38	1.48	V
V_{OL}	Output Low Voltage	1.12	1.02	V
V_{OD}	Output Differential Voltage	0.25	0.46	V
V_{CM}	Output Common Mode Voltage	1.25	1.25	V
I_{DC}	DC Output Current	11.24	10.20	mA

1. For input buffer, see LVDS table.

Typical Building Block Function Performance

Pin-to-Pin Performance (LVCMOS25 12 mA Drive)[1, 2, 3]

Function	–8 Timing	Units
Basic Functions		
16-bit Decoder	4.7	ns
32-bit Decoder	4.7	ns
64-bit Decoder	5.7	ns
4:1 MUX	4.1	ns
8:1 MUX	4.3	ns
16:1 MUX	4.7	ns
32:1 MUX	4.8	ns

1. These functions were generated using the ispLEVER design tool. Exact performance may vary with device and tool version. The tool uses internal parameters that have been characterized but are not tested on every device.
2. Commercial timing numbers are shown. Industrial numbers are typically slower and can be extracted from the Diamond or ispLEVER software.

Register-to-Register Performance[1, 2, 3]

Function	–8 Timing	Units
Basic Functions		
16-bit Decoder	500	MHz
32-bit Decoder	500	MHz
64-bit Decoder	500	MHz
4:1 MUX	500	MHz
8:1 MUX	500	MHz
16:1 MUX	500	MHz
32:1 MUX	445	MHz
8-bit adder	500	MHz
16-bit adder	500	MHz
64-bit adder	305	MHz
16-bit counter	500	MHz
32-bit counter	460	MHz
64-bit counter	320	MHz
64-bit accumulator	315	MHz
Embedded Memory Functions		
512x36 Single Port RAM, EBR Output Registers	340	MHz
1024x18 True-Dual Port RAM (Write Through or Normal, EBR Output Registers)	340	MHz
1024x18 True-Dual Port RAM (Read-Before-Write, EBR Output Registers	130	MHz
1024x18 True-Dual Port RAM (Write Through or Normal, PLC Output Registers)	245	MHz
Distributed Memory Functions		
16x4 Pseudo-Dual Port RAM (One PFU)	500	MHz
32x4 Pseudo-Dual Port RAM	500	MHz
64x8 Pseudo-Dual Port RAM	400	MHz
DSP Function		
18x18 Multiplier (All Registers)	400	MHz
9x9 Multiplier (All Registers)	400	MHz
36x36 Multiply (All Registers)	260	MHz

LatticeECP3 External Switching Characteristics (Continued)[1, 2, 3, 13]

Over Recommended Commercial Operating Conditions

Parameter	Description	Device	–8		–7		–6		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
t_{H_DEL}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-150EA	0.0	—	0.0	—	0.0	—	ns
f_{MAX_IO}	Clock Frequency of I/O and PFU Register	ECP3-150EA	—	500	—	420	—	375	MHz
t_{CO}	Clock to Output - PIO Output Register	ECP3-70EA/95EA	—	3.8	—	4.2	—	4.6	ns
t_{SU}	Clock to Data Setup - PIO Input Register	ECP3-70EA/95EA	0.0	—	0.0	—	0.0	—	ns
t_{H}	Clock to Data Hold - PIO Input Register	ECP3-70EA/95EA	1.4	—	1.6	—	1.8	—	ns
t_{SU_DEL}	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-70EA/95EA	1.3	—	1.5	—	1.7	—	ns
t_{H_DEL}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-70EA/95EA	0.0	—	0.0	—	0.0	—	ns
f_{MAX_IO}	Clock Frequency of I/O and PFU Register	ECP3-70EA/95EA	—	500	—	420	—	375	MHz
t_{CO}	Clock to Output - PIO Output Register	ECP3-35EA	—	3.7	—	4.1	—	4.5	ns
t_{SU}	Clock to Data Setup - PIO Input Register	ECP3-35EA	0.0	—	0.0	—	0.0	—	ns
t_{H}	Clock to Data Hold - PIO Input Register	ECP3-35EA	1.2	—	1.4	—	1.6	—	ns
t_{SU_DEL}	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-35EA	1.3	—	1.4	—	1.5	—	ns
t_{H_DEL}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-35EA	0.0	—	0.0	—	0.0	—	ns
f_{MAX_IO}	Clock Frequency of I/O and PFU Register	ECP3-35EA	—	500	—	420	—	375	MHz
t_{CO}	Clock to Output - PIO Output Register	ECP3-17EA	—	3.5	—	3.9	—	4.3	ns
t_{SU}	Clock to Data Setup - PIO Input Register	ECP3-17EA	0.0	—	0.0	—	0.0	—	ns
t_{H}	Clock to Data Hold - PIO Input Register	ECP3-17EA	1.3	—	1.5	—	1.6	—	ns
t_{SU_DEL}	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-17EA	1.3	—	1.4	—	1.5	—	ns
t_{H_DEL}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-17EA	0.0	—	0.0	—	0.0	—	ns
f_{MAX_IO}	Clock Frequency of I/O and PFU Register	ECP3-17EA	—	500	—	420	—	375	MHz
General I/O Pin Parameters Using Dedicated Clock Input Primary Clock with PLL with Clock Injection Removal Setting[2]									
t_{COPLL}	Clock to Output - PIO Output Register	ECP3-150EA	—	3.3	—	3.6	—	39	ns
t_{SUPLL}	Clock to Data Setup - PIO Input Register	ECP3-150EA	0.7	—	0.8	—	0.9	—	ns
t_{HPLL}	Clock to Data Hold - PIO Input Register	ECP3-150EA	0.8	—	0.9	—	1.0	—	ns
t_{SU_DELPLL}	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-150EA	1.6	—	1.8	—	2.0	—	ns
t_{H_DELPLL}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-150EA	—	0.0	—	0.0	—	0.0	ns
t_{COPLL}	Clock to Output - PIO Output Register	ECP3-70EA/95EA	—	3.3	—	3.5	—	3.8	ns
t_{SUPLL}	Clock to Data Setup - PIO Input Register	ECP3-70EA/95EA	0.7	—	0.8	—	0.9	—	ns

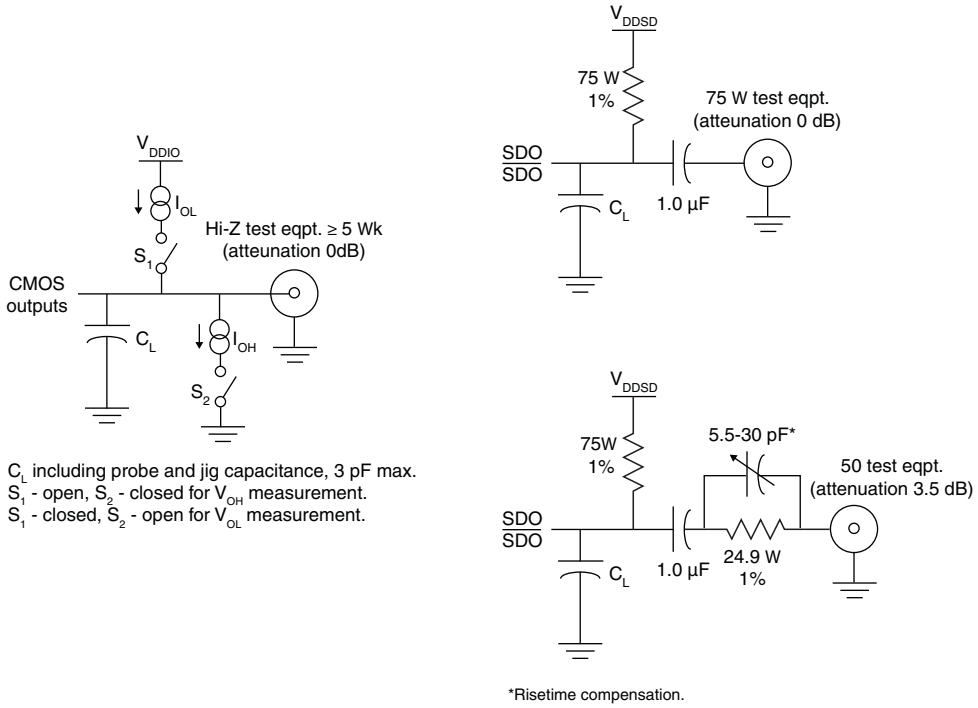
LatticeECP3 External Switching Characteristics (Continued)[1, 2, 3, 13]

Over Recommended Commercial Operating Conditions

Parameter	Description	Device	–8		–7		–6		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
t_{HPLL}	Clock to Data Hold - PIO Input Register	ECP3-70EA/95EA	0.7	—	0.7	—	0.8	—	ns
t_{SU_DELPLL}	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-70EA/95EA	1.6	—	1.8	—	2.0	—	ns
t_{H_DELPLL}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-70EA/95EA	0.0	—	0.0	—	0.0	—	ns
t_{COPLL}	Clock to Output - PIO Output Register	ECP3-35EA	—	3.2	—	3.4	—	3.6	ns
t_{SUPLL}	Clock to Data Setup - PIO Input Register	ECP3-35EA	0.6	—	0.7	—	0.8	—	ns
t_{HPLL}	Clock to Data Hold - PIO Input Register	ECP3-35EA	0.3	—	0.3	—	0.4	—	ns
t_{SU_DELPLL}	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-35EA	1.6	—	1.7	—	1.8	—	ns
t_{H_DELPLL}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-35EA	0.0	—	0.0	—	0.0	—	ns
t_{COPLL}	Clock to Output - PIO Output Register	ECP3-17EA	—	3.0	—	3.3	—	3.5	ns
t_{SUPLL}	Clock to Data Setup - PIO Input Register	ECP3-17EA	0.6	—	0.7	—	0.8	—	ns
t_{HPLL}	Clock to Data Hold - PIO Input Register	ECP3-17EA	0.3	—	0.3	—	0.4	—	ns
t_{SU_DELPLL}	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-17EA	1.6	—	1.7	—	1.8	—	ns
t_{H_DELPLL}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-17EA	0.0	—	0.0	—	0.0	—	ns
Generic DDR[12]									
Generic DDRX1 Inputs with Clock and Data (>10 Bits Wide) Centered at Pin (GDDRX1_RX.SCLK.Centered) Using PCLK Pin for Clock Input									
t_{SUGDDR}	Data Setup Before CLK	All ECP3EA Devices	480	—	480	—	480	—	ps
t_{HOGDDR}	Data Hold After CLK	All ECP3EA Devices	480	—	480	—	480	—	ps
f_{MAX_GDDR}	DDRX1 Clock Frequency	All ECP3EA Devices	—	250	—	250	—	250	MHz
Generic DDRX1 Inputs with Clock and Data (>10 Bits Wide) Aligned at Pin (GDDRX1_RX.SCLK.PLL.Aligned) Using PLLCLKIN Pin for Clock Input									
Data Left, Right, and Top Sides and Clock Left and Right Sides									
$t_{DVACLKGDDR}$	Data Setup Before CLK	All ECP3EA Devices	—	0.225	—	0.225	—	0.225	UI
$t_{DVECLKGDDR}$	Data Hold After CLK	All ECP3EA Devices	0.775	—	0.775	—	0.775	—	UI
f_{MAX_GDDR}	DDRX1 Clock Frequency	All ECP3EA Devices	—	250	—	250	—	250	MHz
Generic DDRX1 Inputs with Clock and Data (>10 Bits Wide) Aligned at Pin (GDDRX1_RX.SCLK.Aligned) Using DLL - CLKIN Pin for Clock Input									
Data Left, Right and Top Sides and Clock Left and Right Sides									
$t_{DVACLKGDDR}$	Data Setup Before CLK	All ECP3EA Devices	—	0.225	—	0.225	—	0.225	UI
$t_{DVECLKGDDR}$	Data Hold After CLK	All ECP3EA Devices	0.775	—	0.775	—	0.775	—	UI
f_{MAX_GDDR}	DDRX1 Clock Frequency	All ECP3EA Devices	—	250	—	250	—	250	MHz
Generic DDRX1 Inputs with Clock and Data (<10 Bits Wide) Centered at Pin (GDDRX1_RX.DQS.Centered) Using DQS Pin for Clock Input									
t_{SUGDDR}	Data Setup After CLK	All ECP3EA Devices	535	—	535	—	535	—	ps
t_{HOGDDR}	Data Hold After CLK	All ECP3EA Devices	535	—	535	—	535	—	ps
f_{MAX_GDDR}	DDRX1 Clock Frequency	All ECP3EA Devices	—	250	—	250	—	250	MHz
Generic DDRX1 Inputs with Clock and Data (<10bits wide) Aligned at Pin (GDDRX1_RX.DQS.Aligned) Using DQS Pin for Clock Input									
Data and Clock Left and Right Sides									
$t_{DVACLKGDDR}$	Data Setup Before CLK	All ECP3EA Devices	—	0.225	—	0.225	—	0.225	UI

Figure 3-19. Test Loads

Test Loads



C_L including probe and jig capacitance, 3 pF max.
S_1 - open, S_2 - closed for V_{OH} measurement.
S_1 - closed, S_2 - open for V_{OL} measurement.

*Risetime compensation.

Timing Jitter Bandpass

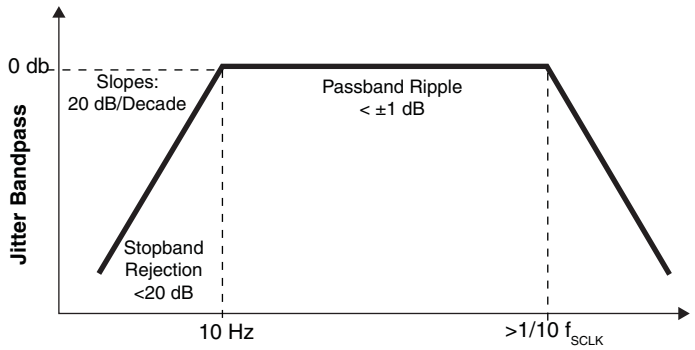


Figure 3-30. SPI Configuration Waveforms

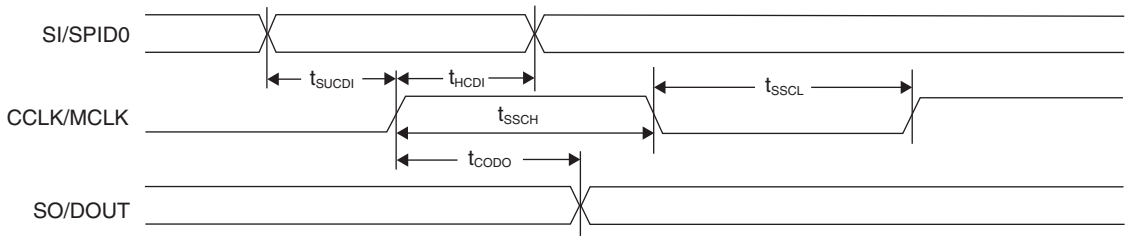
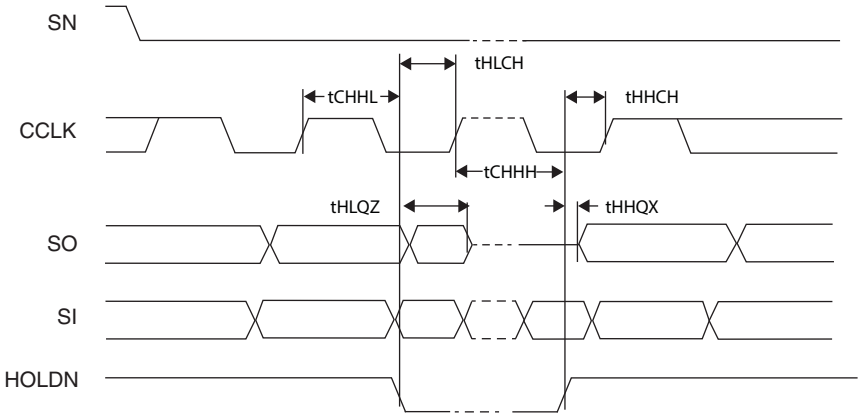


Figure 3-31. Slave SPI HOLDN Waveforms

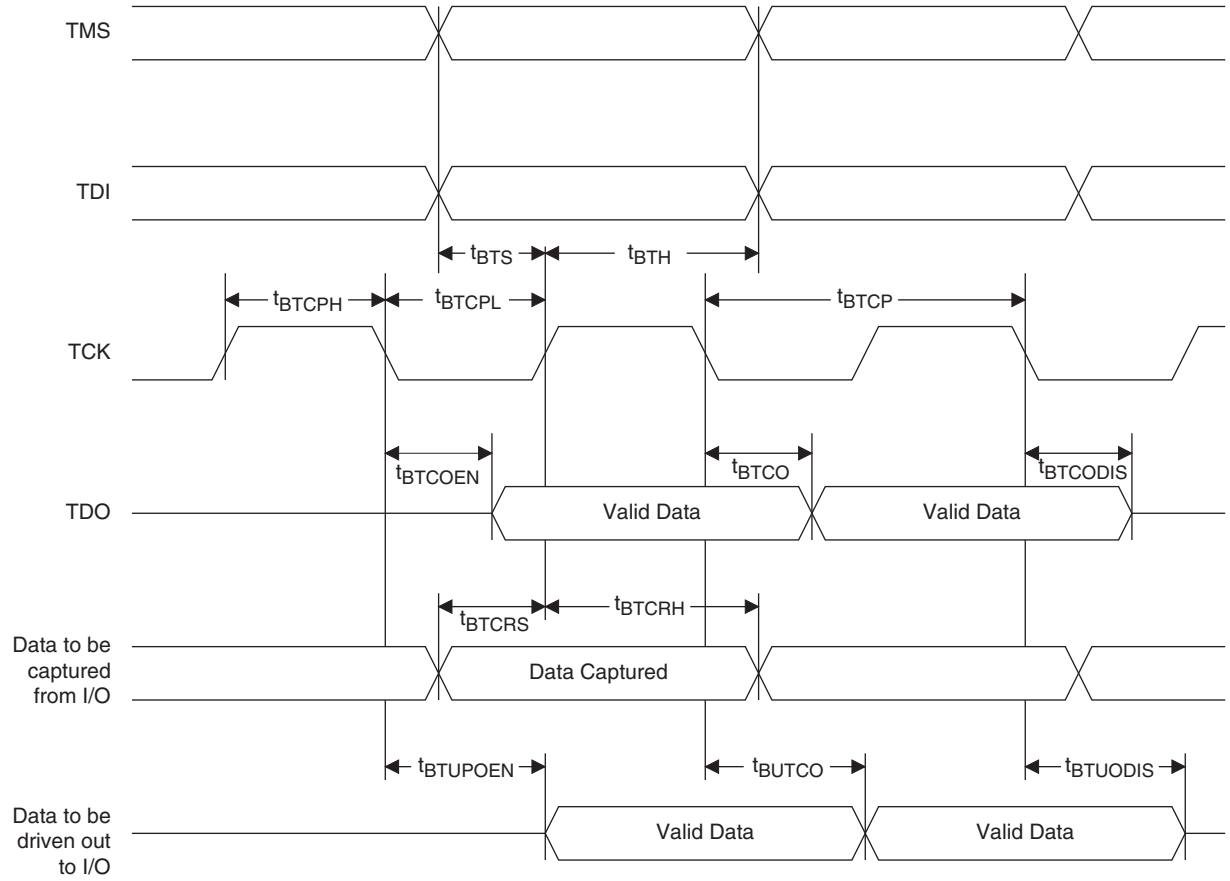


JTAG Port Timing Specifications

Over Recommended Operating Conditions

Symbol	Parameter	Min	Max	Units
f_{MAX}	TCK clock frequency	—	25	MHz
t_{BTCP}	TCK [BSCAN] clock pulse width	40	—	ns
t_{BTCPH}	TCK [BSCAN] clock pulse width high	20	—	ns
t_{BTCPL}	TCK [BSCAN] clock pulse width low	20	—	ns
t_{BTS}	TCK [BSCAN] setup time	10	—	ns
t_{BTH}	TCK [BSCAN] hold time	8	—	ns
t_{BTRF}	TCK [BSCAN] rise/fall time	50	—	mV/ns
t_{BTCO}	TAP controller falling edge of clock to valid output	—	10	ns
$t_{BTCODIS}$	TAP controller falling edge of clock to valid disable	—	10	ns
t_{BTCOEN}	TAP controller falling edge of clock to valid enable	—	10	ns
t_{BTCRS}	BSCAN test capture register setup time	8	—	ns
t_{BTCRH}	BSCAN test capture register hold time	25	—	ns
t_{BUTCO}	BSCAN test update register, falling edge of clock to valid output	—	25	ns
$t_{BTUODIS}$	BSCAN test update register, falling edge of clock to valid disable	—	25	ns
$t_{BTUPOEN}$	BSCAN test update register, falling edge of clock to valid enable	—	25	ns

Figure 3-32. JTAG Port Timing Waveforms



Signal Descriptions (Cont.)

Signal Name	I/O	Description
[LOC]DQS[num]	I/O	DQ input/output pads: T (top), R (right), B (bottom), L (left), DQS, num = ball function number.
[LOC]DQ[num]	I/O	DQ input/output pads: T (top), R (right), B (bottom), L (left), DQ, associated DQS number.
Test and Programming (Dedicated Pins)		
TMS	I	Test Mode Select input, used to control the 1149.1 state machine. Pull-up is enabled during configuration.
TCK	I	Test Clock input pin, used to clock the 1149.1 state machine. No pull-up enabled.
TDI	I	Test Data in pin. Used to load data into device using 1149.1 state machine. After power-up, this TAP port can be activated for configuration by sending appropriate command. (Note: once a configuration port is selected it is locked. Another configuration port cannot be selected until the power-up sequence). Pull-up is enabled during configuration.
TDO	O	Output pin. Test Data Out pin used to shift data out of a device using 1149.1.
VCCJ	—	Power supply pin for JTAG Test Access Port.
Configuration Pads (Used During sysCONFIG)		
CFG[2:0]	I	Mode pins used to specify configuration mode values latched on rising edge of INITN. During configuration, a pull-up is enabled. These are dedicated pins.
INITN	I/O	Open Drain pin. Indicates the FPGA is ready to be configured. During configuration, a pull-up is enabled. It is a dedicated pin.
PROGRAMN	I	Initiates configuration sequence when asserted low. This pin always has an active pull-up. It is a dedicated pin.
DONE	I/O	Open Drain pin. Indicates that the configuration sequence is complete, and the startup sequence is in progress. It is a dedicated pin.
CCLK	I	Input Configuration Clock for configuring an FPGA in Slave SPI, Serial, and CPU modes. It is a dedicated pin.
MCLK	I/O	Output Configuration Clock for configuring an FPGA in SPI, SPIm, and Master configuration modes.
BUSY/SISPI	O	Parallel configuration mode busy indicator. SPI/SPIm mode data output.
CSN/SN/OEN	I/O	Parallel configuration mode active-low chip select. Slave SPI chip select. Parallel burst Flash output enable.
CS1N/HOLDN/RDY	I	Parallel configuration mode active-low chip select. Slave SPI hold input.
WRITEN	I	Write enable for parallel configuration modes.
DOUT/CSON/CSSPI1N	O	Serial data output. Chip select output. SPI/SPIm mode chip select.
D[0]/SPIFASTN	I/O	sysCONFIG Port Data I/O for Parallel mode. Open drain during configuration. sysCONFIG Port Data I/O for SPI or SPIm. When using the SPI or SPIm mode, this pin should either be tied high or low, must not be left floating. Open drain during configuration.
D1	I/O	Parallel configuration I/O. Open drain during configuration.
D2	I/O	Parallel configuration I/O. Open drain during configuration.
D3/SI	I/O	Parallel configuration I/O. Slave SPI data input. Open drain during configuration.
D4/SO	I/O	Parallel configuration I/O. Slave SPI data output. Open drain during configuration.
D5	I/O	Parallel configuration I/O. Open drain during configuration.
D6/SPID1	I/O	Parallel configuration I/O. SPI/SPIm data input. Open drain during configuration.

PICs and DDR Data (DQ) Pins Associated with the DDR Strobe (DQS) Pin

PICs Associated with DQS Strobe	PIO Within PIC	DDR Strobe (DQS) and Data (DQ) Pins
For Left and Right Edges of the Device		
P[Edge] [n-3]	A	DQ
	B	DQ
P[Edge] [n-2]	A	DQ
	B	DQ
P[Edge] [n-1]	A	DQ
	B	DQ
P[Edge] [n]	A	[Edge]DQSn
	B	DQ
P[Edge] [n+1]	A	DQ
	B	DQ
P[Edge] [n+2]	A	DQ
	B	DQ
For Top Edge of the Device		
P[Edge] [n-3]	A	DQ
	B	DQ
P[Edge] [n-2]	A	DQ
	B	DQ
P[Edge] [n-1]	A	DQ
	B	DQ
P[Edge] [n]	A	[Edge]DQSn
	B	DQ
P[Edge] [n+1]	A	DQ
	B	DQ
P[Edge] [n+2]	A	DQ
	B	DQ

Note: “n” is a row PIC number.

LatticeECP3 Family Data Sheet Ordering Information

April 2014 Data Sheet DS1021

LatticeECP3 Part Number Description

LFE3 – XXX XX – X X XXXXXX X

Device Family
ECP3 (LatticeECP3 FPGA + SERDES)

Logic Capacity
17 = 17K LUTs
35 = 33K LUTs
70 = 67K LUTs
95 = 92K LUTs
150 = 149K LUTs

Supply Voltage
EA = 1.2 V

Speed
6 = Slowest
7
8 = Fastest for LatticeECP3-17EA

Grade
C = Commercial
I = Industrial

Package
FTN256 = 256-ball Lead-Free ftBGA
FN484 = 484-ball Lead-Free fpBGA
FN672 = 672-ball Lead-Free fpBGA
FN1156 = 1156-ball Lead-Free fpBGA
MG328 = 328-ball Green csBGA[1]

Power
Blank = Standard Power
L = Low Power

1. Green = Halogen free and lead free.

Ordering Information

LatticeECP3 devices have top-side markings, for commercial and industrial grades, as shown below:

Commercial

LATTICE
LFE3-95EA
7FN672C
Datecode

Industrial

LATTICE
LFE3-95EA
7FN672I
Datecode

Note: See PCN 05A-12 for information regarding a change to the top-side mark logo.

Part Number	Voltage	Grade[1]	Power	Package	Pins	Temp.	LUTs (K)
LFE3-150EA-6FN672I	1.2 V	–6	STD	Lead-Free fpBGA	672	IND	149
LFE3-150EA-7FN672I	1.2 V	–7	STD	Lead-Free fpBGA	672	IND	149
LFE3-150EA-8FN672I	1.2 V	–8	STD	Lead-Free fpBGA	672	IND	149
LFE3-150EA-6LFN672I	1.2 V	–6	LOW	Lead-Free fpBGA	672	IND	149
LFE3-150EA-7LFN672I	1.2 V	–7	LOW	Lead-Free fpBGA	672	IND	149
LFE3-150EA-8LFN672I	1.2 V	–8	LOW	Lead-Free fpBGA	672	IND	149
LFE3-150EA-6FN1156I	1.2 V	–6	STD	Lead-Free fpBGA	1156	IND	149
LFE3-150EA-7FN1156I	1.2 V	–7	STD	Lead-Free fpBGA	1156	IND	149
LFE3-150EA-8FN1156I	1.2 V	–8	STD	Lead-Free fpBGA	1156	IND	149
LFE3-150EA-6LFN1156I	1.2 V	–6	LOW	Lead-Free fpBGA	1156	IND	149
LFE3-150EA-7LFN1156I	1.2 V	–7	LOW	Lead-Free fpBGA	1156	IND	149
LFE3-150EA-8LFN1156I	1.2 V	–8	LOW	Lead-Free fpBGA	1156	IND	149

1. For ordering information on -9 speed grade devices, please contact your Lattice Sales Representative.

Part Number	Voltage	Grade	Power	Package	Pins	Temp.	LUTs (K)
LFE3-150EA-6FN672ITW[1]	1.2 V	–6	STD	Lead-Free fpBGA	672	IND	149
LFE3-150EA-7FN672ITW[1]	1.2 V	–7	STD	Lead-Free fpBGA	672	IND	149
LFE3-150EA-8FN672ITW[1]	1.2 V	–8	STD	Lead-Free fpBGA	672	IND	149
LFE3-150EA-6FN1156ITW[1]	1.2 V	–6	STD	Lead-Free fpBGA	1156	IND	149
LFE3-150EA-7FN1156ITW[1]	1.2 V	–7	STD	Lead-Free fpBGA	1156	IND	149
LFE3-150EA-8FN1156ITW[1]	1.2 V	–8	STD	Lead-Free fpBGA	1156	IND	149

1. Specifications for the LFE3-150EA-*sp*FN*pkg*CTW and LFE3-150EA-*sp*FN*pkg*ITW devices, (where *sp* is the speed and *pkg* is the package), are the same as the LFE3-150EA-*sp*FN*pkg*C and LFE3-150EA-*sp*FN*pkg*I devices respectively, except as specified below.
   - The CTC (Clock Tolerance Circuit) inside the SERDES hard PCS in the TW device is not functional but it can be bypassed and implemented in soft IP.
   - The SERDES XRES pin on the TW device passes CDM testing at 250V.

Date	Version	Section	Change Summary
			LatticeECP3 Maximum I/O Buffer Speed table – Description column, references to VCCIO = 3.0V changed to 3.3V.
			Updated SERDES External Reference Clock Waveforms.
			Transmitter and Receiver Latency Block Diagram – Updated sections of the diagram to match descriptions on the SERDES/PCS Latency Break-down table.
		Pinout Information	"Logic Signal Connections" section heading renamed "Package Pinout Information". Software menu selections within this section have been updated.
			Signal Descriptions table – Updated description for V_{CCA} signal.
April 2012	02.2EA	Architecture	Updated first paragraph of Output Register Block section.
			Updated the information about sysIO buffer pairs below Figure 2-38.
			Updated the information relating to migration between devices in the Density Shifting section.
		DC and Switching Characteristics	Corrected the Definitions in the sysCLOCK PLL Timing table for t_{RST}.
		Ordering Information	Updated topside marks with new logos in the Ordering Information section.
February 2012	02.1EA	All	Updated document with new corporate logo.
November 2011	02.0EA	Introduction	Added information for LatticeECP3-17EA, 328-ball csBGA package.
		Architecture	Added information for LatticeECP3-17EA, 328-ball csBGA package.
		DC and Switching Characteristics	Updated LatticeECP3 Supply Current table power numbers.
			Typical Building Block Function Performance table, LatticeECP3 External Switching Characteristics table, LatticeECP3 Internal Switching Characteristics table and LatticeECP3 Family Timing Adders: Added speed grade -9 and updated speed grade -8, -7 and -6 timing numbers.
		Pinout Information	Added information for LatticeECP3-17EA, 328-ball csBGA package.
		Ordering Information	Added information for LatticeECP3-17EA, 328-ball csBGA package.
			Added ordering information for low power devices and -9 speed grade devices.
July 2011	01.9EA	DC and Switching Characteristics	Removed ESD Performance table and added reference to LatticeECP3 Product Family Qualification Summary document.
			sysCLOCK PLL TIming table, added footnote 4.
			External Reference Clock Specification table – removed reference to VREF-CM-AC and removed footnote for VREF-CM-AC.
		Pinout Information	Pin Information Summary table: Corrected VCCIO Bank8 data for LatticeECP3-17EA 256-ball ftBGA package and LatticeECP-35EA 256-ball ftBGA package.
April 2011	01.8EA	Architecture	Updated Secondary Clock/Control Sources text section.
		DC and Switching Characteristics	Added data for 150 Mbps to SERDES Power Supply Requirements table.
			Updated Frequencies in Table 3-6 Serial Output Timing and Levels
			Added Data for 150 Mbps to Table 3-7 Channel Output Jitter
			Corrected External Switching Characteristics table, Description for DDR3 Clock Timing, t_{JIT}.
			Corrected Internal Switching Characteristics table, Description for EBR Timing, t_{SUWREN_EBR} and t_{HWREN_EBR}.
			Added footnote 1 to sysConfig Port Timing Specifications table.
			Updated description for RX-CIDs to 150M in Table 3-9 Serial Input Data Specifications